



## General Description

FSMOS<sup>®</sup> MOSFET is based on Oriental Semiconductor's unique device design to achieve low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. The high  $V_{th}$  series is specially designed to use in power supply systems with driving voltage of more than 10V.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery



## Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switching mode power supply

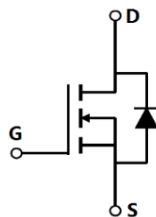
## Key Performance Parameters

| Parameter                         | Value | Unit      |
|-----------------------------------|-------|-----------|
| $V_{DS}$                          | 60    | V         |
| $I_D$ , pulse                     | 800   | A         |
| $R_{DS(ON)}$ , max @ $V_{GS}=10V$ | 1.5   | $m\Omega$ |
| $Q_g$                             | 86    | nC        |

## Marking Information

| Product Name  | Package | Marking      |
|---------------|---------|--------------|
| SFS06R012UGNF | PDFN5x6 | SFS06R012UGN |

## Package & Pin information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

| Parameter                                                                 | Symbol                | Value      | Unit               |
|---------------------------------------------------------------------------|-----------------------|------------|--------------------|
| Drain-source voltage                                                      | $V_{DS}$              | 60         | V                  |
| Gate-source voltage                                                       | $V_{GS}$              | $\pm 20$   | V                  |
| Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$         | $I_D$                 | 210        | A                  |
| Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{D, \text{pulse}}$ | 800        | A                  |
| Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$ | $I_S$                 | 210        | A                  |
| Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{S, \text{pulse}}$ | 800        | A                  |
| Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$                | $P_D$                 | 170        | W                  |
| Single pulsed avalanche energy <sup>5)</sup>                              | $E_{AS}$              | 462        | mJ                 |
| Operation and storage temperature                                         | $T_{stg}, T_j$        | -55 to 150 | $^{\circ}\text{C}$ |

**Thermal Characteristics**

| Parameter                                          | Symbol          | Value | Unit                 |
|----------------------------------------------------|-----------------|-------|----------------------|
| Thermal resistance, junction-case                  | $R_{\theta JC}$ | 0.73  | $^{\circ}\text{C/W}$ |
| Thermal resistance, junction-ambient <sup>4)</sup> | $R_{\theta JA}$ | 62    | $^{\circ}\text{C/W}$ |

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

| Parameter                        | Symbol       | Min. | Typ. | Max. | Unit          | Test condition                                  |
|----------------------------------|--------------|------|------|------|---------------|-------------------------------------------------|
| Drain-source breakdown voltage   | $BV_{DSS}$   | 60   |      |      | V             | $V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$ |
| Gate threshold voltage           | $V_{GS(th)}$ | 2    |      | 4    | V             | $V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$     |
| Drain-source on-state resistance | $R_{DS(ON)}$ |      | 1.2  | 1.5  | m $\Omega$    | $V_{GS}=10\text{ V}, I_D=30\text{ A}$           |
| Gate-source leakage current      | $I_{GSS}$    |      |      | 100  | nA            | $V_{GS}=20\text{ V}$                            |
|                                  |              |      |      | -100 |               | $V_{GS}=-20\text{ V}$                           |
| Drain-source leakage current     | $I_{DSS}$    |      |      | 1    | $\mu\text{A}$ | $V_{DS}=60\text{ V}, V_{GS}=0\text{ V}$         |
| Gate resistance                  | $R_G$        |      | 1.8  |      | $\Omega$      | $f=1\text{ MHz}$ , Open drain                   |

### Dynamic Characteristics

| Parameter                    | Symbol       | Min. | Typ. | Max. | Unit | Test condition                                                                             |
|------------------------------|--------------|------|------|------|------|--------------------------------------------------------------------------------------------|
| Input capacitance            | $C_{iss}$    |      | 6060 |      | pF   | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=25\text{ V}$ ,<br>$f=100\text{ kHz}$                      |
| Output capacitance           | $C_{oss}$    |      | 2690 |      | pF   |                                                                                            |
| Reverse transfer capacitance | $C_{rss}$    |      | 101  |      | pF   |                                                                                            |
| Turn-on delay time           | $t_{d(on)}$  |      | 46   |      | ns   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=30\text{ V}$ ,<br>$R_G=2\ \Omega$ ,<br>$I_D=30\text{ A}$ |
| Rise time                    | $t_r$        |      | 44   |      | ns   |                                                                                            |
| Turn-off delay time          | $t_{d(off)}$ |      | 110  |      | ns   |                                                                                            |
| Fall time                    | $t_f$        |      | 42   |      | ns   |                                                                                            |

### Gate Charge Characteristics

| Parameter            | Symbol        | Min. | Typ. | Max. | Unit | Test condition                                                        |
|----------------------|---------------|------|------|------|------|-----------------------------------------------------------------------|
| Total gate charge    | $Q_g$         |      | 86   |      | nC   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=30\text{ V}$ ,<br>$I_D=30\text{ A}$ |
| Gate-source charge   | $Q_{gs}$      |      | 27   |      | nC   |                                                                       |
| Gate-drain charge    | $Q_{gd}$      |      | 21   |      | nC   |                                                                       |
| Gate plateau voltage | $V_{plateau}$ |      | 5.1  |      | V    |                                                                       |

### Body Diode Characteristics

| Parameter                     | Symbol    | Min. | Typ. | Max. | Unit | Test condition                                                                 |
|-------------------------------|-----------|------|------|------|------|--------------------------------------------------------------------------------|
| Diode forward voltage         | $V_{SD}$  |      |      | 1.3  | V    | $I_S=30\text{ A}$ ,<br>$V_{GS}=0\text{ V}$                                     |
| Reverse recovery time         | $t_{rr}$  |      | 83   |      | ns   | $V_R=30\text{ V}$ ,<br>$I_S=30\text{ A}$ ,<br>$di/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge       | $Q_{rr}$  |      | 158  |      | nC   |                                                                                |
| Peak reverse recovery current | $I_{rrm}$ |      | 3    |      | A    |                                                                                |

### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^{\circ}\text{C}$ .
- 5)  $V_{DD}=50\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=0.5\text{ mH}$ , starting  $T_j=25\text{ }^{\circ}\text{C}$ .

## Electrical Characteristics Diagrams

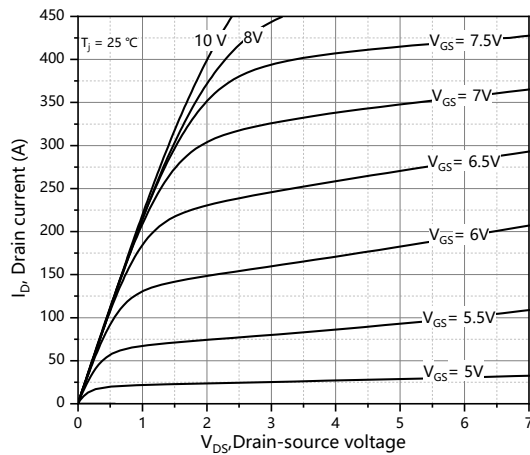


Figure 1. Typ. output characteristics

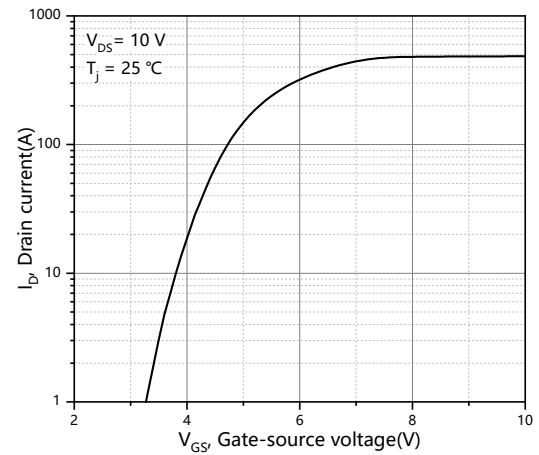


Figure 2. Typ. transfer characteristics

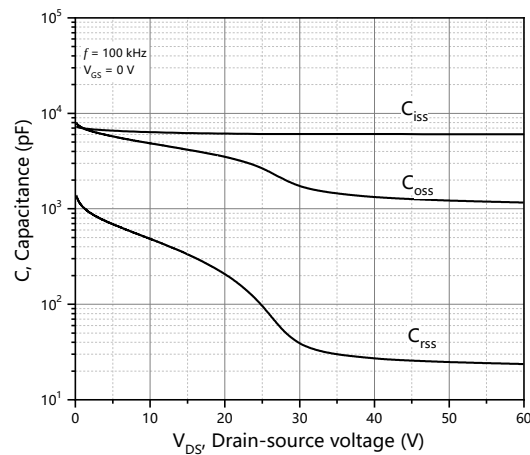


Figure 3. Typ. capacitances

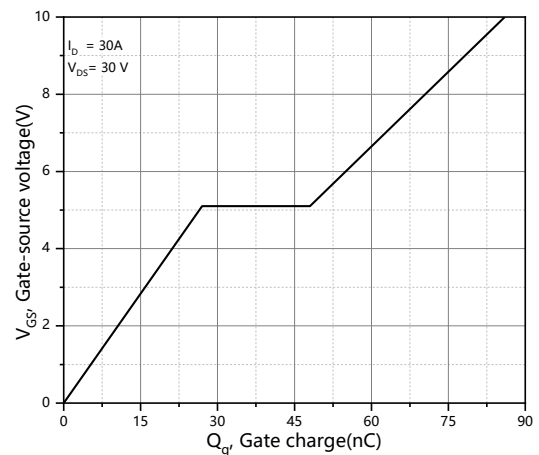


Figure 4. Typ. gate charge

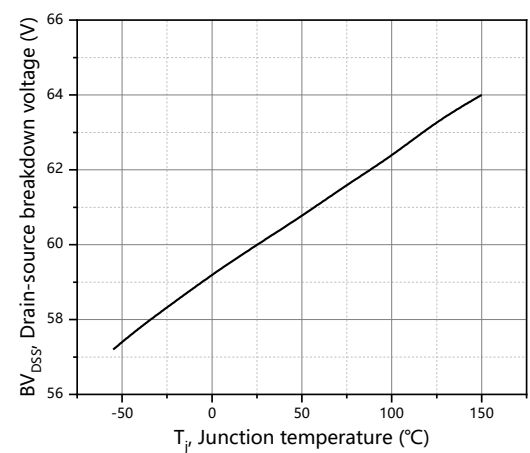


Figure 5. Drain-source breakdown voltage

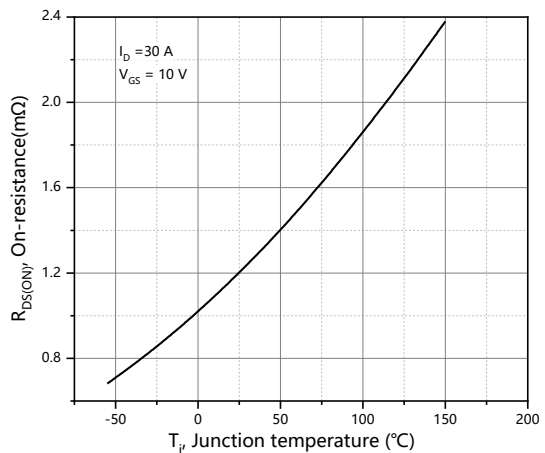
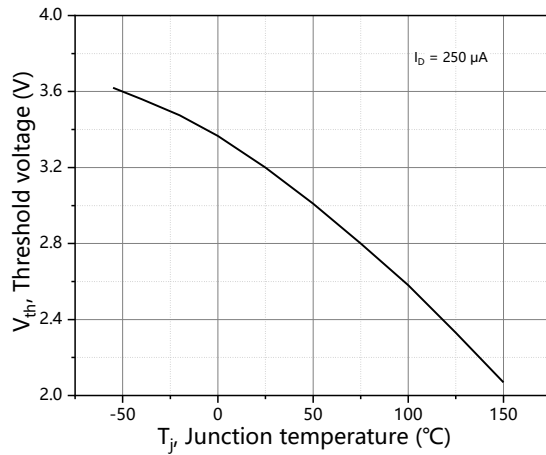
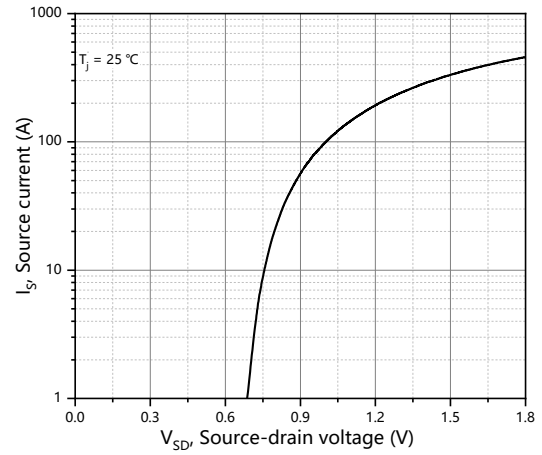


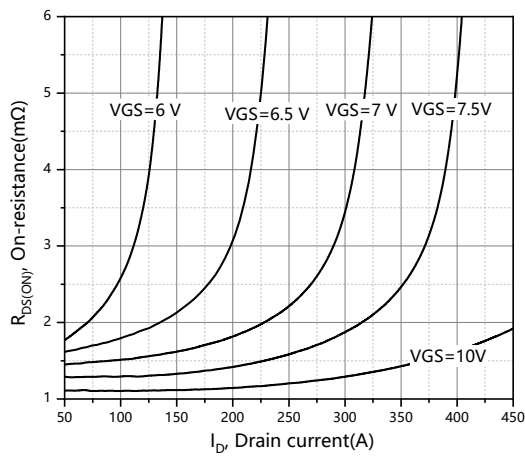
Figure 6. Drain-source on-state resistance



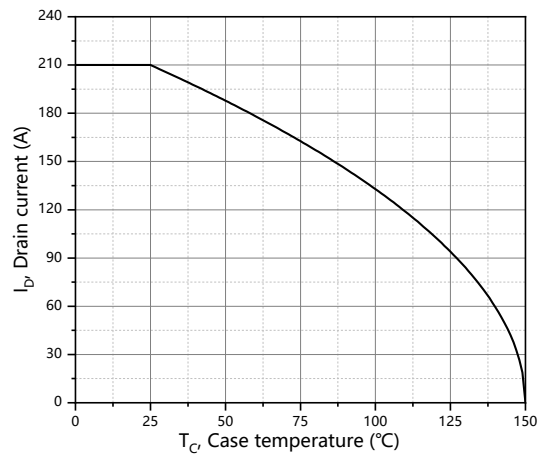
**Figure 7. Threshold voltage**



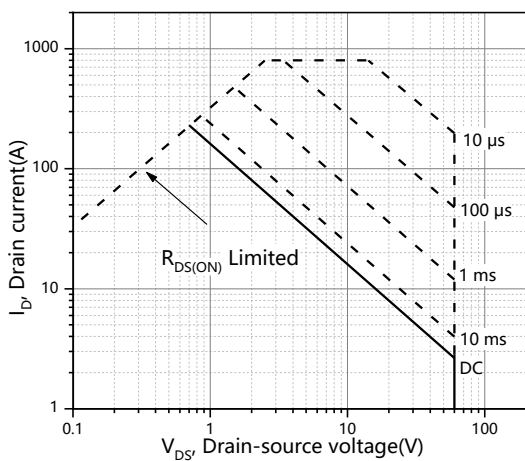
**Figure 8. Forward characteristic of body diode**



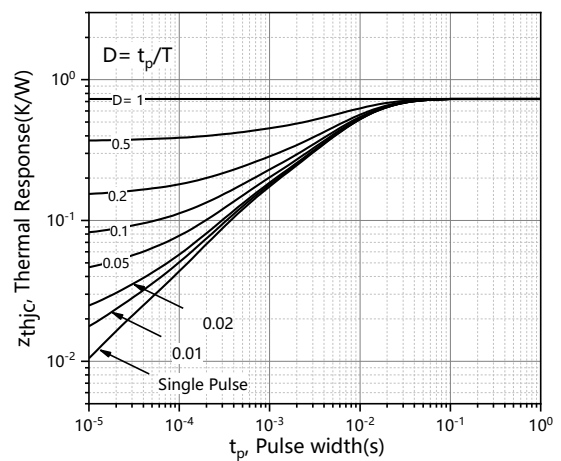
**Figure 9. Drain-source on-state resistance**



**Figure 10. Drain current**

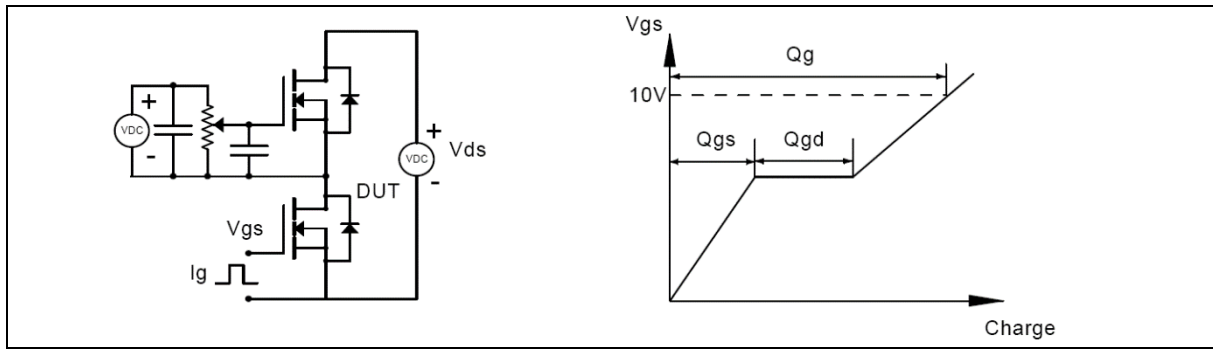


**Figure 11. Safe operation area  $T_C=25^{\circ}\text{C}$**

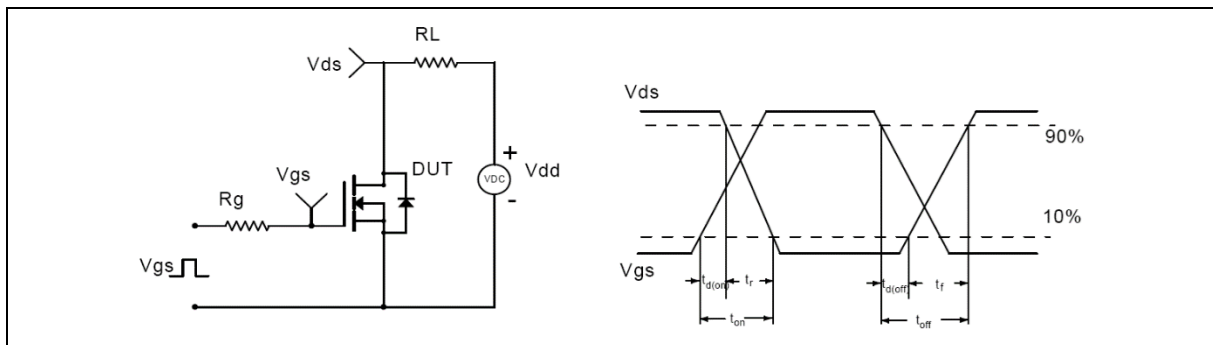


**Figure 12. Max. transient thermal impedance**

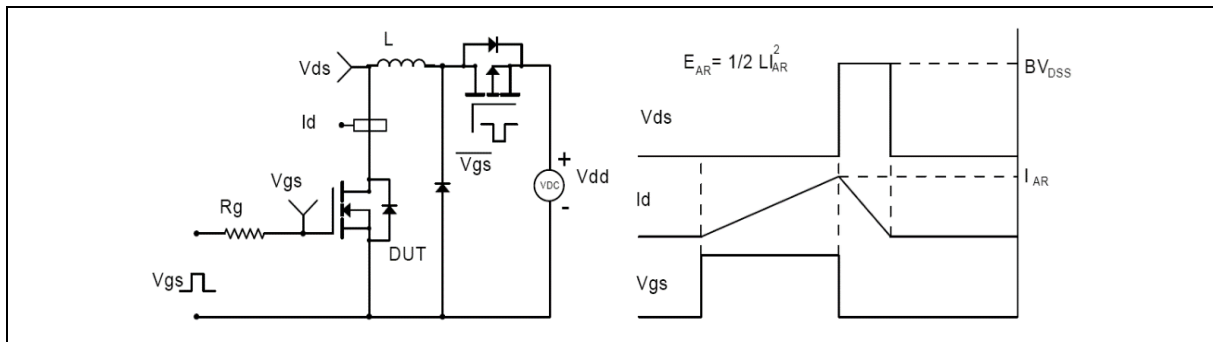
## Test circuits and waveforms



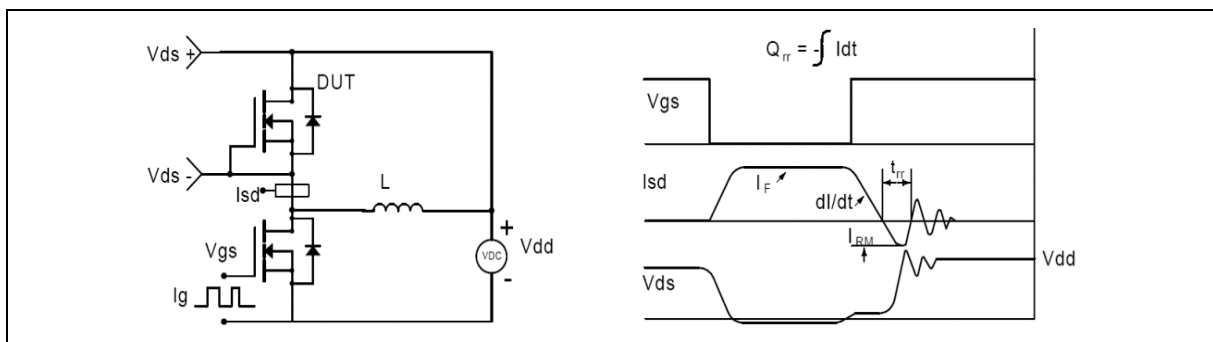
**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

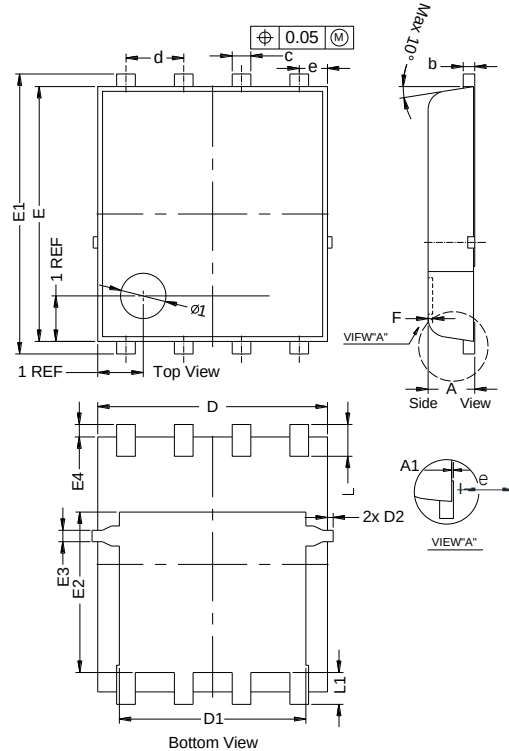


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

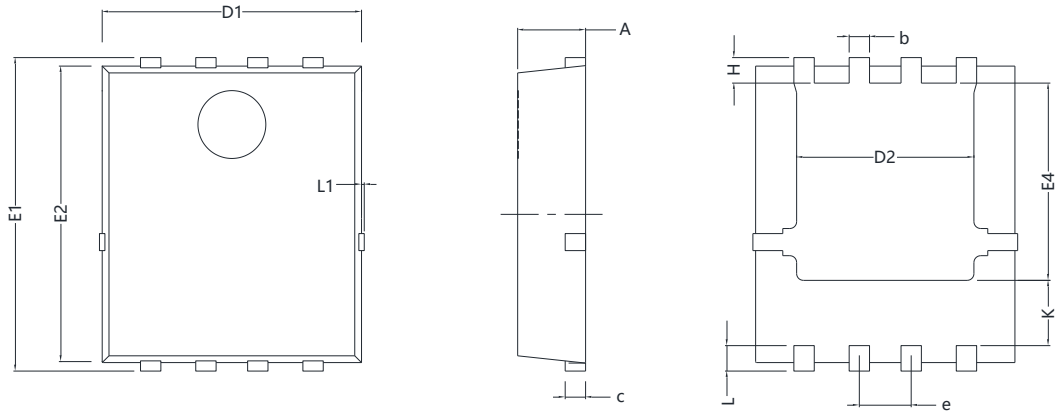
## Package Information



| Symbol | mm       |       |       |
|--------|----------|-------|-------|
|        | Min      | Nom   | Max   |
| A      | 0.90     | 1.00  | 1.10  |
| A1     | 0.00     | -     | 0.05  |
| b      | 0.246    | 0.254 | 0.312 |
| c      | 0.31     | 0.41  | 0.51  |
| d      | 1.27 BSC |       |       |
| D      | 4.95     | 5.05  | 5.15  |
| D1     | 4.00     | 4.10  | 4.20  |
| D2     | -        | -     | 0.125 |
| e      | 0.62 BSC |       |       |
| E      | 5.50     | 5.60  | 5.70  |
| E1     | 6.05     | 6.15  | 6.25  |
| E2     | 3.425    | 3.525 | 3.625 |
| E3     | 0.15     | 0.25  | 0.35  |
| E4     | 0.175    | 0.275 | 0.375 |
| F      | -        | -     | 0.10  |
| L      | 0.50     | 0.60  | 0.70  |
| L1     | 0.60     | 0.70  | 0.80  |
| K      | 1.125    | 1.225 | 1.325 |

Version : PDFN5x6-H package outline dimension

## Package Information



| Symbol | mm        |       |       |
|--------|-----------|-------|-------|
|        | Min       | Nom   | Max   |
| A      | 1.00      | 1.10  | 1.20  |
| b      | 0.30      | 0.40  | 0.50  |
| c      | 0.154     | 0.254 | 0.354 |
| D1     | 5.05      | 5.25  | 5.45  |
| D2     | 3.80      | 4.10  | 4.25  |
| E1     | 5.95      | 6.15  | 6.35  |
| E2     | 5.76      | 5.86  | 5.96  |
| E4     | 3.90      | 4.10  | 4.30  |
| e      | 1.27 BSC  |       |       |
| H      | 0.295     | 0.395 | 0.495 |
| K      | 1.055 REF |       |       |
| L      | 0.30      | 0.60  | 0.70  |
| L1     | 0.01      | 0.05  | 0.12  |

Version : PDFN5×6-PL package outline dimension



**Ordering Information**

| Package Type | Units/ Reel | Reels / Inner Box | Units/ Inner Box | Inner Boxes/ Carton Box | Units/ Carton Box |
|--------------|-------------|-------------------|------------------|-------------------------|-------------------|
| PDFN5x6-H    | 5000        | 2                 | 10000            | 5                       | 50000             |
| PDFN5x6-P    | 5000        | 2                 | 10000            | 5                       | 50000             |

**Product Information**

| Product       | Package | Pb Free | RoHS | Halogen Free |
|---------------|---------|---------|------|--------------|
| SFS06R012UGNF | PDFN5x6 | yes     | yes  | yes          |

**Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Oriental Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

For further information on technology, delivery terms and conditions and prices, please contact the Oriental Semiconductor sales representatives ([www.orientalsemi.com](http://www.orientalsemi.com)).

© Oriental Semiconductor Co.,Ltd. All Rights Reserved 

| Version | Revision History      | Date       |
|---------|-----------------------|------------|
| V1.0    | Initial release       | 2023-06-14 |
| V1.1    | Add assembly site "P" | 2025-07-28 |